

LISTING OF CLAIMS:

Claim Amdt.

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gmd 8/30/07

AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions and listings of claims in the application:

LISTING OF CLAIMS:

1. (previously presented): A self-supported III-V nitride semiconductor substrate having a substantially uniform carrier concentration distribution at least on its outermost surface, wherein said substrate has a carrier concentration of $1 \times 10^{17} \text{ cm}^{-3}$ or more, and wherein variations in the carrier concentration are within $\pm 25\%$ in said outermost surface, said variations in the carrier concentration lying in a surface (in-plane) thereof.

2. (previously presented): The self-supported III-V nitride semiconductor substrate according to claim 1, wherein said substantially uniform carrier concentration distribution in a surface layer exists from the top surface to a depth of at least $10 \text{ }\mu\text{m}$.

Claims 3-9 canceled.

10. (previously presented): A III-V nitride semiconductor substrate having a substantially uniform carrier concentration distribution at least on its outermost surface, wherein said substrate has a carrier concentration of less than $1 \times 10^{17} \text{ cm}^{-3}$, and wherein variations in the carrier concentration are within $\pm 100\%$ in said outermost surface, said variations in the carrier concentration lying in a surface (in-plane) thereof.

Claims 11-12 canceled.

13. (previously presented): The III-V nitride semiconductor substrate according to claim 1 or 2, wherein variations in the carrier concentration are not larger on a top surface of said substrate than on a bottom surface of said substrate.